

IN THE CLAIMS

Please substitute the claim set in the appendix entitled Clean Version of Pending Claims for the previously pending claim set. The substitute claim set is intended to reflect amendment of previously pending claims 40, 55, 99, 110, 113, 122, 124, 134, and addition of new claims 136-141. The specific amendments to individual claims are detailed in the following marked up set of claims.

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40. (Currently Amended): A method of fabricating a photovoltaic device, comprising:

- providing a substrate;
- forming an electrode first film on the substrate;
- forming a semiconductor second film on the electrode first film;
- forming a semiconductor third film on the semiconductor second film; and
- forming an electrode fourth film on the semiconductor third film

wherein one of forming the second film and forming the third film includes:

- depositing semiconductor material using a deposition source; and
- supplying focussed ion energy from a secondary source to the semiconductor material to deposit the semiconductor material into a desired film structure.

41. (Original): The method of claim 40, wherein supplying energy includes supplying energized particles having energy of greater than about 5eV.

42. (Original): The method of claim 40, wherein supplying energy includes supplying energized particles having energy of less than about 3000eV.

43. (Original): The method of claim 40, wherein supplying energy includes supplying energized particles having energy in the range of about 5eV to about 500 eV.

44. (Original): The method of claim 40, wherein supplying energy includes supplying energized particles having energy in the range of about 5eV to about 250 eV.

45. (Original): The method of claim 40, wherein supplying energy includes supplying energized particles having energy in the range of about 10eV to about 200 eV.
46. (Original): The method of claim 40, wherein supplying energy includes supplying energized particles having energy in the range of about 20 eV to about 40 eV.
47. (Original): The method of claim 40, wherein forming the second film includes depositing CdS.
48. (Original): The method of claim 40, wherein forming the third film includes depositing CdTe.
49. (Original): The method of claim 40, wherein forming the second film includes the supplying energy, and wherein the supplying energy includes supplying ionized sulfur.
50. (Original): The method of claim 49, wherein forming the second film includes depositing cadmium and reacting the cadmium with the ionized sulfur.
51. (Original): The method of claim 40, wherein forming the third film includes the supplying energy, and wherein the supplying energy includes supplying energized ions.
52. (Original): The method of claim 51, wherein forming the third film includes depositing cadmium.
53. (Original): The method of claim 40, wherein supplying energy includes supplying ions simultaneously with depositing material from the deposition source.
54. (Original): The method of claim 40, wherein supplying energy includes supplying oxygen ions.

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55. (Currently Amended): The method of claim 40, wherein supplying energy includes supplying a noble gas ions.

56. (Original): The method of claim 40, wherein the substrate is not heated during forming the second film or the third film.

57. (Original): The method of claim 40, wherein forming the semiconductor third film on the semiconductor second film includes depositing a high quality first region and then depositing a second highly doped region on the first region.

58. (Original): The method of claim 40, wherein the one of forming the second film and forming the third film includes providing energy to the semiconductor material being deposited by only means sending the semiconductor material toward the cell and by the means supplying energy.

78. (Previously added): A photovoltaic cell made according to the method of claim 40.

79. (Previously added): A photovoltaic cell made according to the method of claim 40, further wherein

the substrate is essentially transparent;

the electrode first film formed on the substrate is essentially transparent;

a semiconductor second film on the electrode first film;

a semiconductor third film on the semiconductor second film; and

an electrode fourth film on the semiconductor third film,

wherein the third film includes a high quality first region adjacent to the second film and a highly doped second region remote from the second film, and the first region and the second film form a pn junction of the photovoltaic cell.

80. (Previously added): The method of claim 40, wherein the method is performed within a chamber and wherein the chamber has a temperature of less than about 300 degrees Celsius during the depositing of the semiconductor material.

81. (Previously added): The method of claim 40, wherein the method is performed within a chamber and wherein the chamber has a temperature of less than about 250 degrees Celsius during the depositing of the semiconductor material.

82. (Previously added): The method of claim 40, further comprising holding the substrate below about 500 degrees Celsius during the depositing of the semiconductor material.

83. (Previously added): The method of claim 40, wherein the chamber is adapted to hold the substrate below about 300 degrees Celsius during the depositing of the semiconductor material.

84. (Previously added): The method of claim 40, wherein the chamber is adapted to hold the substrate below about 200 degrees Celsius during the depositing of the semiconductor material.

85. (Previously added): The method of claim 40, wherein supplying energy includes supplying energized particles having energy of less than about 5000eV.

86. (Previously added): The method of claim 40, wherein supplying energy includes supplying energized particles having energy of less than about 1000eV.

87. (Previously added): The method of claim 40, wherein supplying energy includes supplying energized particles having energy of less than about 500eV.

88. (Previously added): The method of claim 40, wherein supplying energy includes supplying energized particles having energy of less than about 300eV.

89. (Previously added): The method of claim 40, wherein supplying energy includes supplying energized particles that are focused at the surface where the film is being formed.

90. (Previously added): The method of claim 40, wherein forming the second film includes depositing ZnS.

91. (Previously added): The method of claim 40, wherein forming the second film includes depositing CdZnS.

92. (Previously added): The method of claim 40, wherein forming the second film includes depositing CdO.

93. (Previously added): The method of claim 40, wherein forming the second film includes depositing ZnO.

94. (Previously added): The method of claim 40, wherein forming the second film includes depositing CdZnO.

95. (Previously added): The method of claim 40, wherein forming the second film includes depositing SiC.

96. (Previously added): The method of claim 40, wherein forming the second film includes depositing GaN.

97. (Previously added): The method of claim 40, wherein forming the second film includes depositing InGaN.

98. (Previously added): The method of claim 40, wherein forming the second film includes depositing AlGa_N.

B38 99. (Currently Amended): The method of claim 40, wherein forming the third film includes depositing ~~CuInSe₂~~ CuInSe₂.

100. (Previously added): The method of claim 40, wherein forming the third film includes depositing InP.

101. (Previously added): The method of claim 40, wherein forming the third film includes depositing GaAs.

102. (Previously added): The method of claim 40, wherein forming the third film includes depositing InGaAs.

103. (Previously added): The method of claim 40, wherein forming the third film includes depositing InGaP.

104. (Previously added): The method of claim 40, wherein forming the third film includes depositing Si.

105. (Previously added): The method of claim 40, wherein the providing the substrate further includes dispensing the substrate from a roll of substrate material.

106. (Currently Amended): The method of claim ~~107~~ 105, further comprising passing the substrate over a curved thermally controlled object.

B39 107. (Currently Amended): The method of claim ~~108~~ 106, wherein the curved thermally controlled object is a rotatable drum.

108. (Previously added): The method of claim 40, wherein forming the third film includes depositing a high-quality region adjacent the second film followed by a highly doped bulk region.

109. (Previously added): The method of claim 40, wherein the electrode first film is substantially transparent, and further comprising
forming first and second conductive leads contacting the transparent second film and the electrode fourth film, respectively, to carry power away from the photovoltaic device.

B40 110. (Currently Amended): The method of claim 40, wherein forming the second film includes depositing n-type ~~polycrystalline~~ polycrystalline CdS, and wherein forming the third film includes depositing p-type ~~polycrystalline~~ polycrystalline CdTe.

111. (Currently Amended): The method of claim ~~112~~ 110, wherein the second film is about 50nm thick.

112. (Previously added): The method of claim 40, wherein the second film is about 50nm thick.

B41 113. (Currently Amended): A method of fabricating a photovoltaic device, comprising:
providing a substrate;
forming an electrode first film on the substrate;
forming a semiconductor second film on the electrode first film;
forming a semiconductor third film on the semiconductor second film; and
forming an electrode fourth film on the semiconductor third film
wherein the forming of the second film includes:
depositing semiconductor material using a deposition source; and
supplying focussed ion energy from a secondary source to the semiconductor material to deposit the semiconductor material into a desired film structure.

114. (Previously added): The method of claim 113, wherein supplying energy includes supplying energized particles having energy in the range of about 5eV to about 250 eV.

115. (Previously added): The method of claim 113, wherein supplying energy includes supplying energized particles having energy in the range of about 10eV to about 200 eV.

116. (Previously added): The method of claim 113, wherein forming the second film includes depositing CdS and forming the third film includes depositing CdTe.

117. (Previously added): The method of claim 113, wherein the providing the substrate further includes dispensing the substrate from a roll of substrate material.

118. (Previously added): The method of claim 113, further comprising passing the substrate over a curved thermally controlled object.

119. (Previously added): The method of claim 118, wherein the curved thermally controlled object is a rotatable drum.

120. (Previously added): The method of claim 113, wherein forming the third film includes depositing a high-quality region adjacent the second film followed by a highly doped bulk region.

121. (Previously added): The method of claim 113, wherein the electrode first film is substantially transparent, and further comprising

forming first and second conductive leads contacting the ~~transparent second electrode~~ first film and the electrode fourth film, respectively, to carry power away from the photovoltaic device.

B42 122. (Currently Amended): The method of claim 113, wherein forming the second film includes depositing n-type ~~polycrystalline~~ polycrystalline CdS, and wherein forming the third film includes depositing p-type ~~polycrystalline~~ polycrystalline CdTe.

123. (Previously added): The method of claim 113, wherein the second film is about 50nm thick.

B43 124. (Currently Amended): A method of fabricating a photovoltaic device, comprising:
providing a substrate;
forming an electrode first film on the substrate;
forming a semiconductor second film on the electrode first film;
forming a semiconductor third film on the semiconductor second film; and
forming an electrode fourth film on the semiconductor third film
wherein the forming of the third film includes:
depositing semiconductor material using a deposition source; and
supplying focussed ion energy from a secondary source to the semiconductor material to deposit the semiconductor material into a desired film structure.

125. (Previously added): The method of claim 124, wherein supplying energy includes supplying energized particles having energy in the range of about 5eV to about 250 eV.

126. (Previously added): The method of claim 125, wherein supplying energy includes supplying energized particles having energy in the range of about 10eV to about 200 eV.

127. (Previously added): The method of claim 124, wherein the forming of the second film includes depositing CdS and the forming of the third film includes depositing CdTe.

128. (Previously added): The method of claim 124, wherein the providing the substrate further includes dispensing the substrate from a roll of substrate material.

129. (Previously added): The method of claim 124, further comprising passing the substrate over a curved thermally controlled object.

130. (Previously added): The method of claim 129, wherein the curved thermally controlled object is controlled to balance the effect of heat generated on the substrate and films thereon during the deposition.

131. (Previously added): The method of claim 130, wherein the curved thermally controlled object is a rotatable drum.

132. (Previously added): The method of claim 124, wherein forming the third film includes depositing a high-quality region adjacent the second film followed by a highly doped bulk region.

133. (Previously added): The method of claim 124, wherein the electrode first film is substantially transparent, and further comprising
forming first and second conductive leads contacting the ~~transparent second electrode~~
first film and the electrode fourth film, respectively, to carry power away from the photovoltaic device.

B44 134. (Currently Amended): The method of claim 124, wherein forming the second film includes depositing n-type ~~polycrystalline~~ polycrystalline CdS, and wherein forming the third film includes depositing p-type ~~polycrystalline~~ polycrystalline CdTe.

135. (Previously added): The method of claim 124, wherein the second film is about 50nm thick.

B45 136. (Currently added): The method of claim 124, wherein the supplying focussed energy includes supplying energized ions focussed at the film surface.

137. (Currently added): The method of claim 136, wherein the supplying focussed energy includes supplying energized argon ions.

138. (Currently added): The method of claim 136, wherein the supplying focussed energy includes supplying energized xenon ions.

139. (Currently added): The method of claim 136, wherein the supplying focussed energy includes supplying energized sulphur ions that form a sulfide film.

140. (Currently added): The method of claim 136, wherein the supplying focussed energy includes supplying energized oxygen ions that form an oxide film.

141. (Currently added): The method of claim 136, wherein the supplying focussed energy includes controlling a quality of a physical interface between the second film and the third film.
